
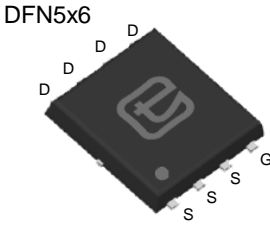
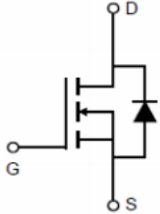


**60V N-Channel DTMOS**

<b>Features</b> <ul style="list-style-type: none"> <li>● Trench Power DTMOS Technology</li> <li>● Low <math>R_{DS(ON)}</math></li> <li>● Low Gate Charge</li> <li>● Optimized for Fast-switching Applications</li> </ul>		<b>Product Summary</b>	
<b>Applications</b> <ul style="list-style-type: none"> <li>● Synchronous Rectification in DC/DC and AC/DC Converters</li> <li>● Isolated DC/DC Converters in Telecom and Industrial</li> </ul>		$V_{DS}$ 60V $R_{DS(ON)}$ (at $V_{GS}=10V$ ) < 15m $\Omega$ $R_{DS(ON)}$ (at $V_{GS}=4.5V$ ) < 19m $\Omega$ $I_D$ (at $V_{GS}=10V$ ) 45A 100% UIS Tested	
			
<b>Device</b>	<b>Package</b>	<b>Marking</b>	
TSG10N06AT	DFN5×6	10N06AT	

**Absolute Maximum Ratings**  $T_C = 25^\circ C$ , unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	60	V
Continuous Drain Current	$I_D$	$T_C = 25^\circ C$	45
		$T_C = 100^\circ C$	27
Pulsed Drain Current (note1)	$I_{DM}$	180	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	20	mJ
Avalanche Current (note1)	$I_{AS}$	20	A
Power Dissipation ( $T_C = 25^\circ C$ )	$P_D$	56.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+175	$^\circ C$

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	2.1	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	50	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
			Min.	Typ.	Max.			
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	--	--	V		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$		
		$V_{DS} = 60V, V_{GS} = 0V, T_J = 100^\circ\text{C}$	--	--	100			
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	--	2.5	V		
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	--	12	15	m $\Omega$		
		$V_{GS} = 4.5V, I_D = 18A$	--	15	19			
Forward Transconductance (Note3)	$g_{fs}$	$V_{DS} = 5V, I_D = 20A$	--	100	--	S		
<b>Dynamic</b>								
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0\text{MHz}$	--	1134	--	pF		
Output Capacitance	$C_{oss}$		--	123	--			
Reverse Transfer Capacitance	$C_{rss}$		--	12	--			
Total Gate Charge	$Q_g(10V)$	$V_{DD} = 30V, I_D = 20A,$ $V_{GS} = 10V$	--	21	--	nC		
	$Q_g(4.5V)$		--	11	--			
Gate-Source Charge	$Q_{gs}$		--	3.1	--			
Gate-Drain Charge	$Q_{gd}$		--	5.1	--			
Turn-on Delay Time	$t_{d(on)}$		$V_{DD} = 30V, I_D = 20A,$ $R_G = 3\Omega$	--	7		--	ns
Turn-on Rise Time	$t_r$			--	3		--	
Turn-off Delay Time	$t_{d(off)}$	--		20	--			
Turn-off Fall Time	$t_f$	--		3	--			
<b>Drain-Source Body Diode Characteristics</b>								
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	30	A		
Pulsed Diode Forward Current	$I_{SM}$		--	--	90			
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 1A, V_{GS} = 0V$	--	0.72	1	V		
Reverse Recovery Time	$t_{rr}$	$I_F = 20A,$ $di_F/dt = 500A/\mu s$	--	17	--	ns		
Reverse Recovery Charge	$Q_{rr}$		--	60	--	nC		

**Notes**

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{AS} = 20A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

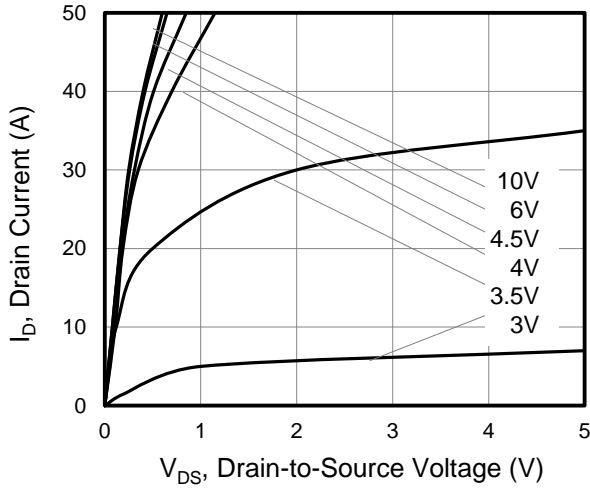


Figure 2. Transfer Characteristics

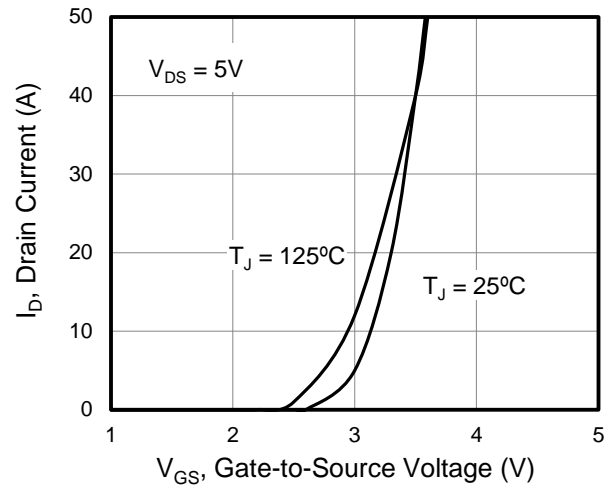


Figure 3. On-Resistance vs. Drain Current

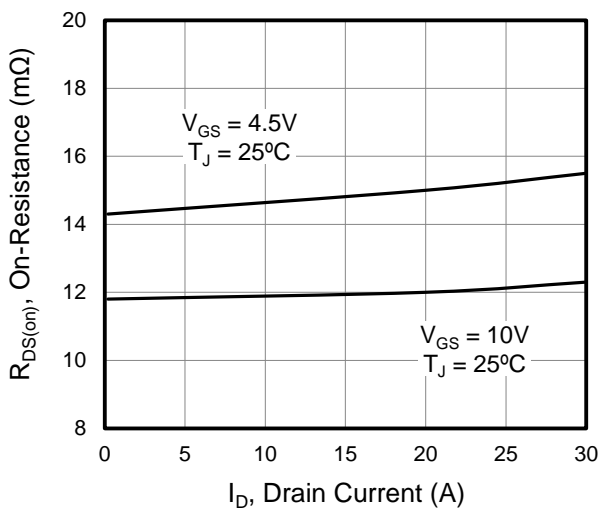


Figure 4. Capacitance

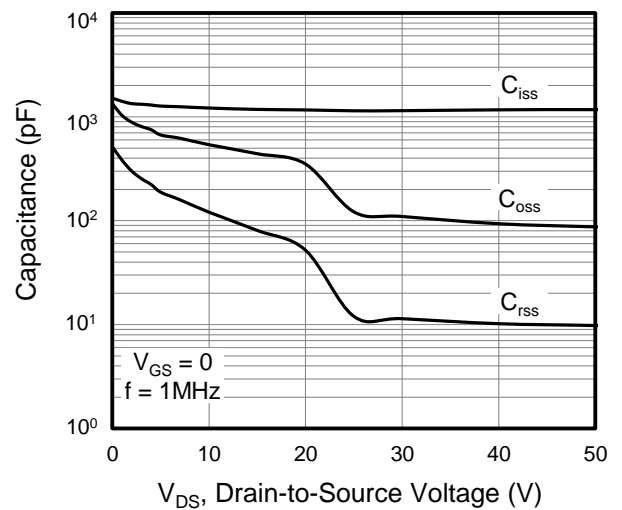


Figure 5. Gate Charge

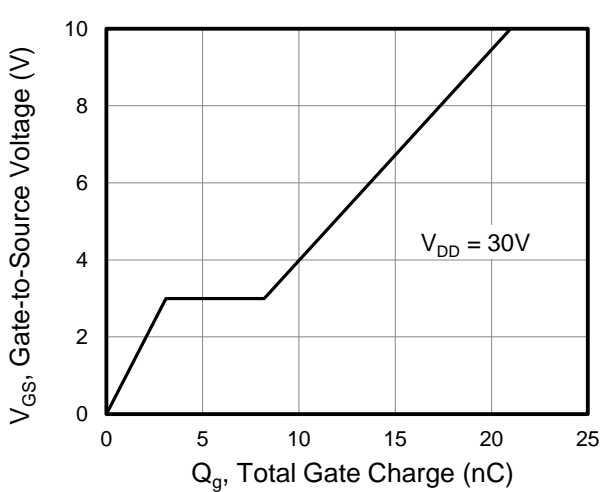
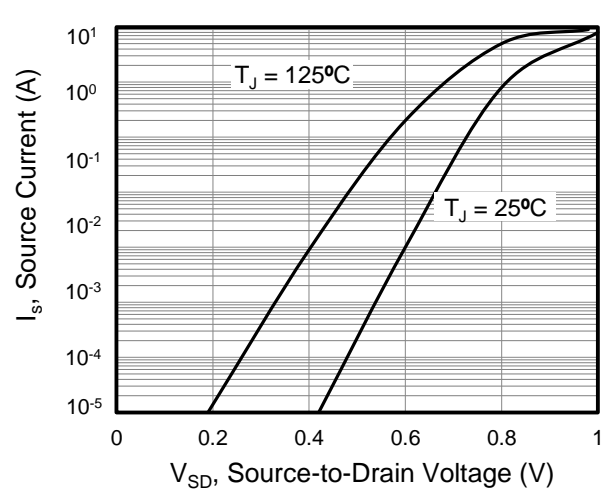


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

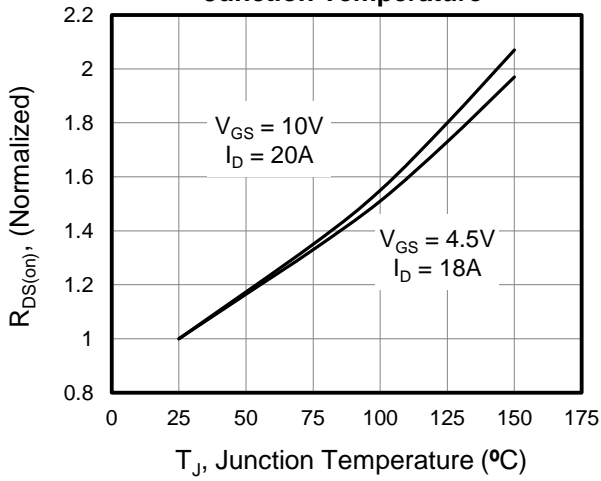


Figure 8. Threshold Voltage vs. Junction Temperature

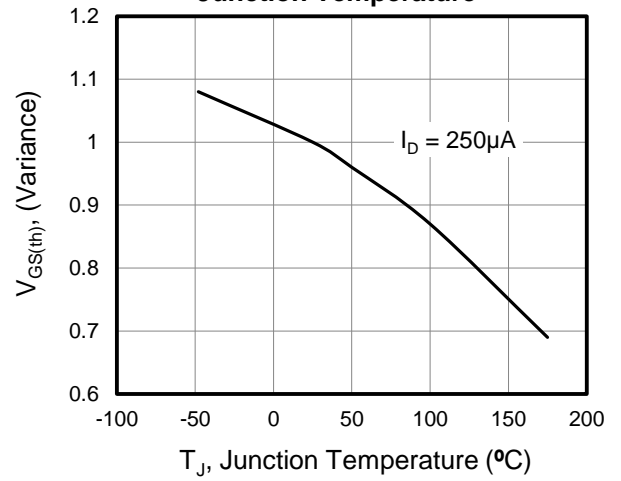


Figure 9. Transient Thermal Impedance

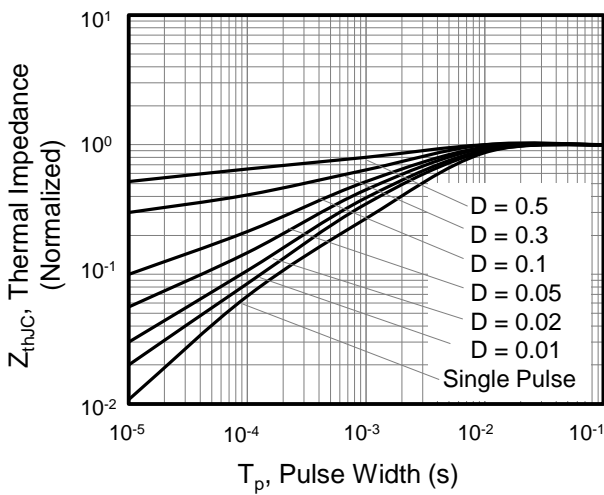


Figure 10. Safe operation area

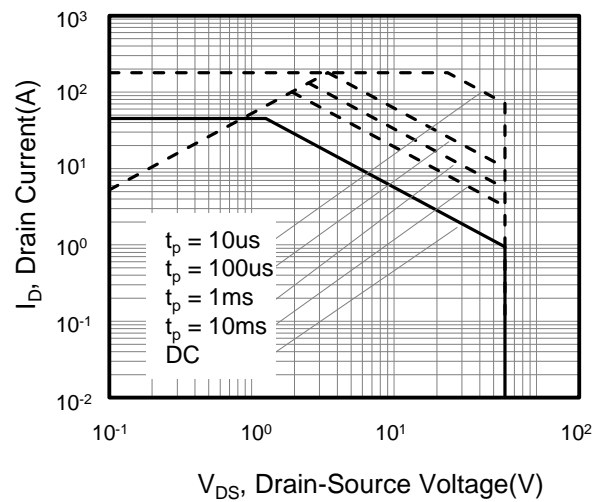




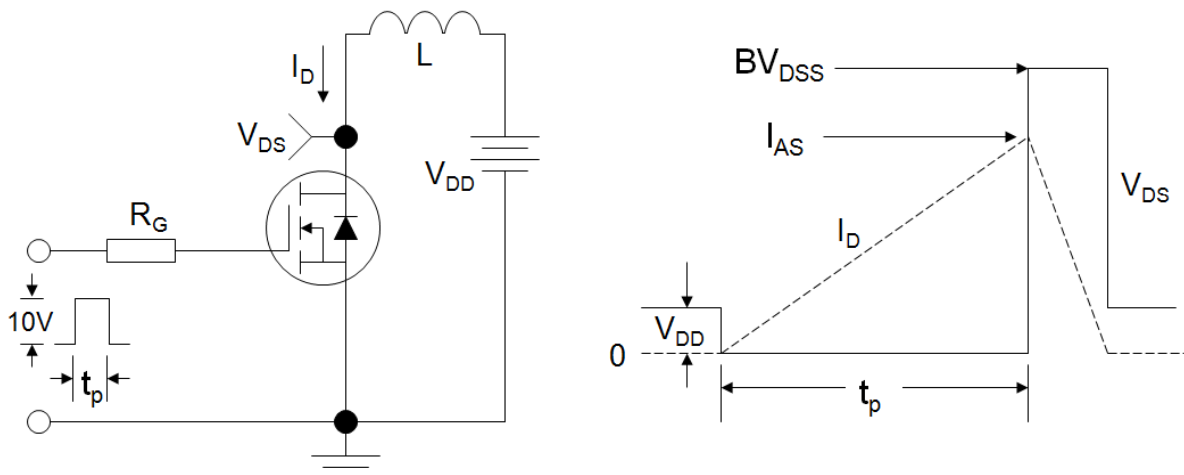
Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

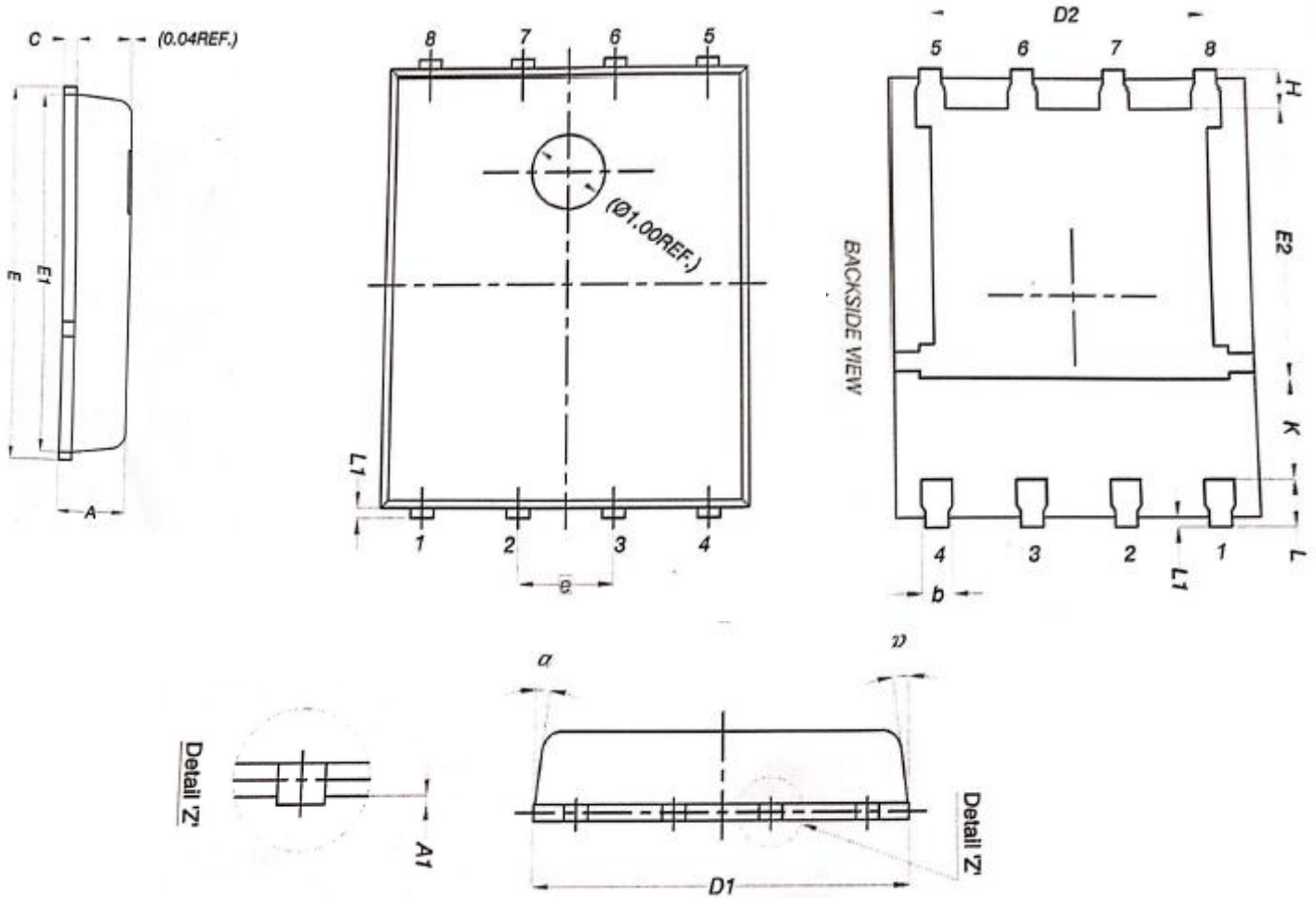


Figure C: Unclamped Inductive Switching Test Circuit and Waveform

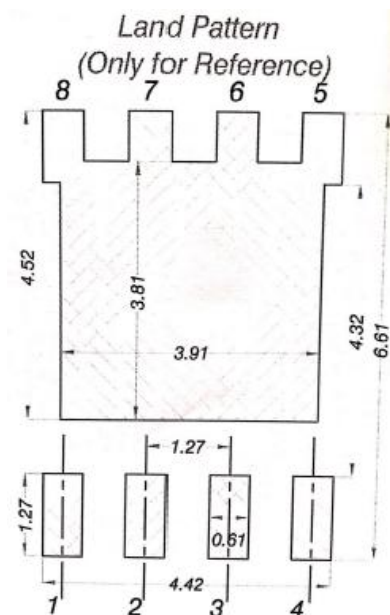




DFN5×6 PACKAGR OUTLINE



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
$\square$	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
$\alpha$	0°	-	12°





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